



Silicon Gate MOS 8308

8192 BIT STATIC MOS READ ONLY MEMORY Organization -- 1024 Words x 8 Bits

- Fast Access — 450 ns
- Directly Compatible with 8080 CPU at Maximum Processor Speed
- Two Chip Select Inputs for Easy Memory Expansion
- Directly TTL Compatible — All Inputs and Outputs
- Three State Output — OR-Tie Capability
- Fully Decoded
- Standard Power Supplies +12V DC, ±5V DC

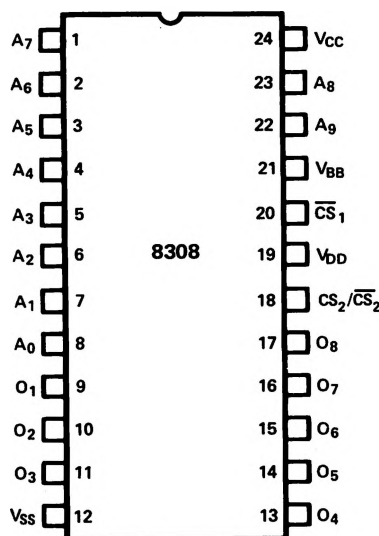
The Intel® 8308 is an 8,192 bit static MOS mask programmable Read Only Memory organized as 1024 words by 8-bits. This ROM is designed for 8080 microcomputer system applications where high performance, large bit storage, and simple interfacing are important design objectives. The inputs and outputs are fully TTL compatible.

A pin for pin compatible electrically programmed erasable ROM, the Intel® 8708, is available for system development and small quantity production use.

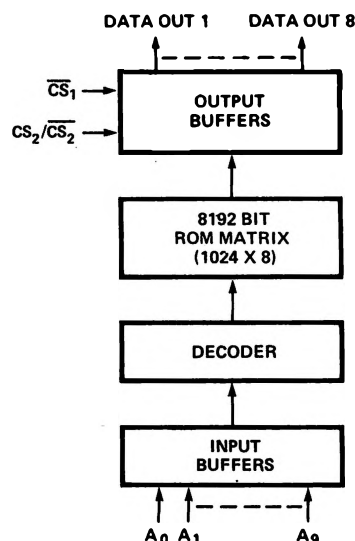
Two Chip Selects are provided — $\overline{CS}_1$ which is negative true, and $CS_2/\overline{CS}_2$ which may be programmed either negative or positive true at the mask level.

The 8308 read only memory is fabricated with N-channel silicon gate technology. This technology provides the designer with high performance, easy-to-use MOS circuits.

PIN CONFIGURATION



BLOCK DIAGRAM



PIN NAMES

A ₀ - A ₉	ADDRESS INPUTS
O ₁ - O ₈	DATA OUTPUTS
CS ₁ , CS ₂	CHIP SELECT INPUTS

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Absolute Maximum Ratings*

Ambient Temperature Under Bias -25°C to $+85^{\circ}\text{C}$
 Storage Temperature -65°C to $+150^{\circ}\text{C}$
 Voltage On Any Pin With Respect
 To V_{BB} -0.3V to 20V
 Power Dissipation 1.0 Watt

*COMMENT

Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

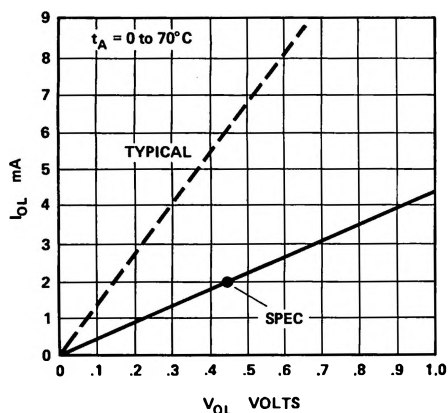
D.C. and Operating Characteristics

$T_A = 0^{\circ}\text{C}$ to $+70^{\circ}\text{C}$, $V_{\text{CC}} = 5\text{V} \pm 5\%$; $V_{\text{DD}} = 12\text{V} \pm 5\%$, $V_{\text{BB}} = -5\text{V} \pm 5\%$, $V_{\text{SS}} = 0\text{V}$ Unless Otherwise Specified.

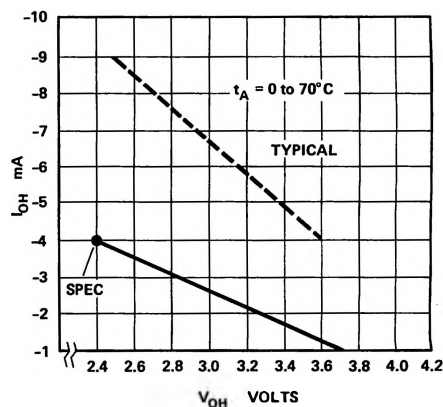
Symbol	Parameter	Limits			Unit	Test Conditions
		Min.	Typ.[1]	Max.		
I_{LI}	Input Load Current (All Input Pins Except $\overline{\text{CS}}_1$)			10	μA	$V_{\text{IN}} = 0$ to 5.25V
I_{LCL}	Input Load Current on $\overline{\text{CS}}_1$			1.6	mA	$V_{\text{IN}} = 0.45\text{V}$
I_{LPC}	Input Peak Load Current on $\overline{\text{CS}}_1$			4	mA	$V_{\text{IN}} = 0.8\text{V}$ to 3.3V
I_{LKC}	Input Leakage Current on $\overline{\text{CS}}_1$			10	μA	$V_{\text{IN}} = 3.3\text{V}$ to 5.25V
I_{LO}	Output Leakage Current			10	μA	Chip Deselected
V_{IL}	Input "Low" Voltage	$V_{\text{SS}} - 1$		0.8V	V	
V_{IH}	Input "High" Voltage	3.3		$V_{\text{CC}} + 1.0$	V	
V_{OL}	Output "Low" Voltage			0.45	V	$I_{\text{OL}} = 2\text{mA}$
V_{OH1}	Output "High" Voltage	2.4			V	$I_{\text{OH}} = -4\text{mA}$
V_{OH2}	Output "High" Voltage	3.7			V	$I_{\text{OH}} = -1\text{mA}$
I_{CC}	Power Supply Current V_{CC}		.8	2	mA	
I_{DD}	Power Supply Current V_{DD}		32	60	mA	
I_{BB}	Power Supply Current V_{BB}		$10\mu\text{A}$	1	mA	
P_{D}	Power Dissipation			775	mW	

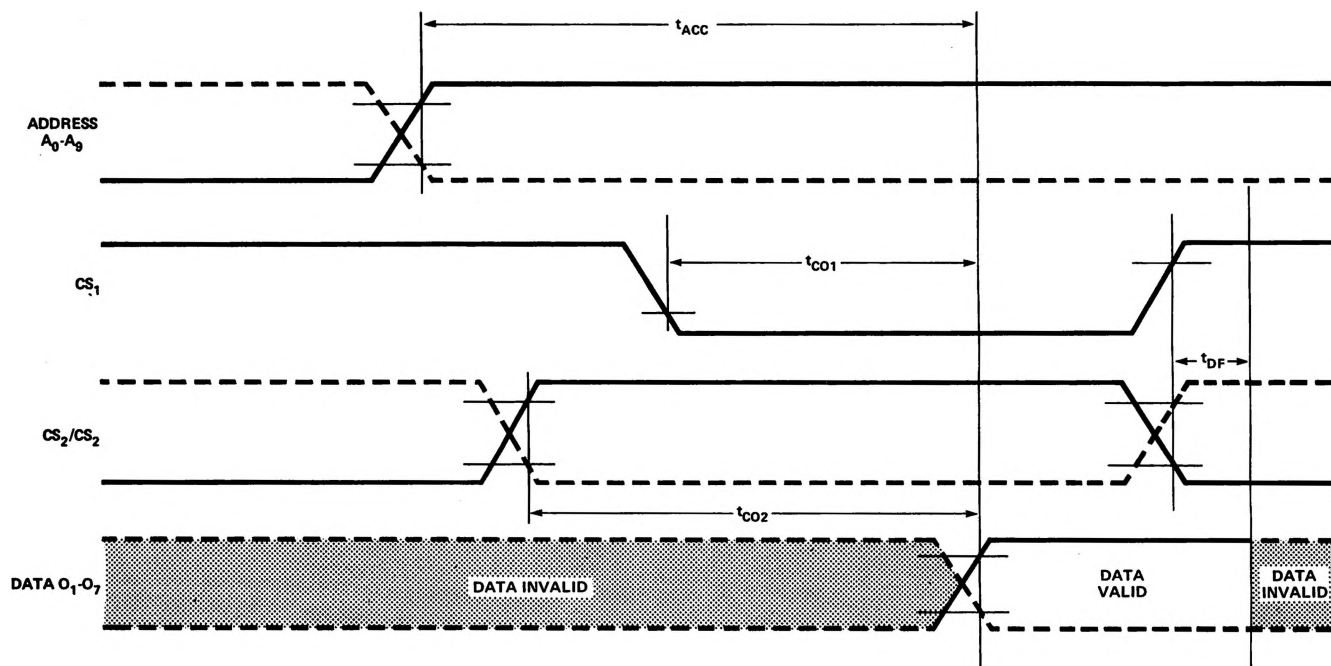
NOTE 1: Typical values for $T_A = 25^{\circ}\text{C}$ and nominal supply voltage

D.C. OUTPUT CHARACTERISTICS



D.C. OUTPUT CHARACTERISTICS

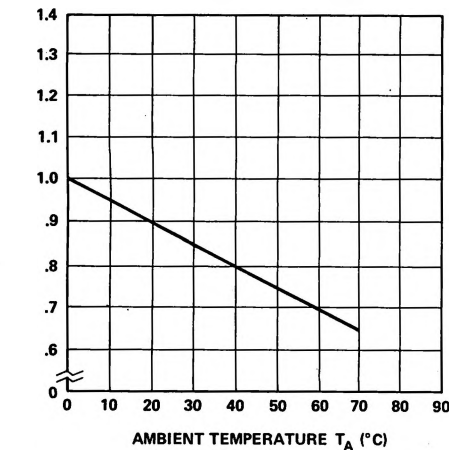




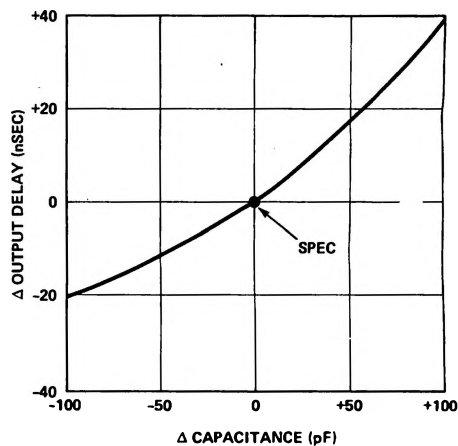
SILICON GATE MOS 8308

Typical Characteristics (Nominal supply voltages unless otherwise noted.)

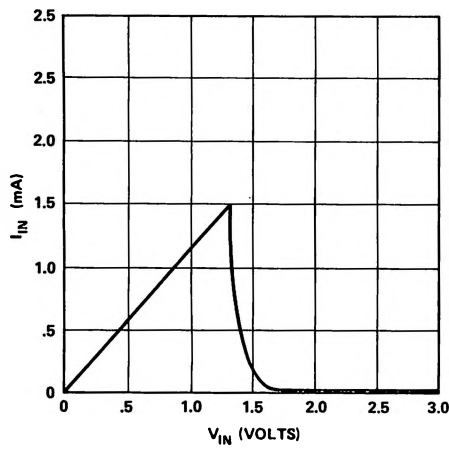
**I_{DD} VS. TEMPERATURE
(NORMALIZED)**



**Δ OUTPUT CAPACITANCE
VS. Δ OUTPUT DELAY**



**$\overline{CS}_1$ INPUT
CHARACTERISTICS**



**T_{ACC} VS. TEMPERATURE
(NORMALIZED)**

